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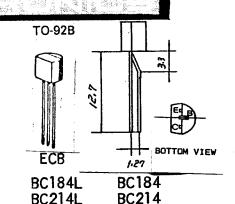
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## BC183, L . BC213, L

COMPLEMENTARY SILICON AF SMALL SIGNAL AMPLIFIERS & DRIVERS

The BC183, BC183L (NPN) & BC213, BC213L (PNP) are complementary silicon planar epitaxial transistors for use in AF small signal amplifiers and drivers, as well as for low power universal applications. Both types feature good linearity of D.C. current gain.



ABSOLUTE MAXIMUM RATINGS		BC183,L	BC213,L
Collector-Base Voltage	$V_{CBO}$	45V	45V
Collector-Emitter Voltage	V <sub>CEO</sub>	30 V	30 V
Emitter-Base Voltage	$V_{EBO}$	6V	5V
Collector Current	$I_{C}$		200mA
Total Power Dissipation @ T <sub>A</sub> =25 <sup>o</sup> C Derate above 25 <sup>o</sup> C	P <sub>tot</sub>	300mW 2.4mW/°C	
Operating Junction and Storage Temperature	$T_{j}, T_{stg}$	-55 to	+150°C

## ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	MIN TYP	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	30		٧	I <sub>C</sub> =2mA I <sub>B</sub> =0
Collector-Base Breakdown Voltage	BVCB0	45		٧	IC=10μA IE=0
Emitter-Base Breakdown Voltage BC183,L BC213,L	BVEB0	6 5		٧	I <b>g</b> =10μΑ IC=0
Collector Cutoff Current	ICBO	-	15	nA	V <sub>CB</sub> =30V I <sub>E</sub> =0
Emitter Cutoff Current	IEBO		15	nA	VEB=4V IC=0

FAX: 3-410321

## ELECTRICAL CHARACTERISTICS (TA=25°C)

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Collector-Emitter Sa		VCE(sat)	İ			V	
	BC18 <u>3</u> ,L BC21 <u>3</u> ,L			0.07	0.25		IC=10mA IB=0.5mA
					0.6		IC=100mA IB=5mA*
Base-Emitter Saturat	ion	VBE(sat)				V	IC=100mA IB=5mA*
	BC183,L BC213,L				1.2		;
Base-Emitter Voltage		V <sub>BE</sub>				V	V <sub>CE</sub> =5V I <sub>C</sub> =2mA
	BC183,L BC213,L		0.55 0.6		0.7 0.72		
D.C. Current Gain		HFE	100				V <sub>CE</sub> =5V I <sub>C</sub> =10μA
	BC183,L BC213,L		220 140				VCE=5V IC=2mA
	BC18 <u>3</u> ,L BC21 <u>3</u> ,L		130	120			V <sub>CE</sub> =5V I <sub>C</sub> =100mA*
Small Signal Current	Gain	h <sub>fe</sub>					
(f=1KHz)	BC183,L		240		900		VCE=5V IC=2mA
	BC213,L Group A Group B Group C		140 125 240 450		<b>260</b> 500 900		
Output Capacitance	BC18 <u>3</u> ,L BC21 <u>3</u> ,L	Cob		3 5	5	pF	.VCB=10V IE=0 f=1MHz
Input Capacitance	BC18 <u>3</u> ,L	C <sub>ib</sub>		9.5		pF	VEB=0.5V IE=0 f=1MHz
Current Gain-Bandwid Product	th	fŢ				MHz	IC=10mA VCE=5V f=100MHz
	BC183,L BC213,L		,	280 350	·		
Noise Figure	BC18 <u>3</u> ,L BC21 <u>3</u> ,L	NF			10	dB	IC=200μA VCE=5V RG=2KΩ NB=15.7KHz f1=10Hz f2=10KHz

<sup>\*</sup> Pulse Test : Pulse Width =  $300\mu S$ , Duty Cycle  $\leq 2\%$ .